



# 2SK213, 2SK214, 2SK215, 2SK216

Silicon N Channel MOS FET

REJ03G0903-0200  
(Previous: ADE-208-1241)  
Rev.2.00  
Sep 07, 2005

## Application

High frequency and low frequency power amplifier, high speed switching.

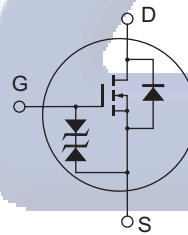
Complementary pair with 2SJ76, J77, J78, J79

## Features

- Suitable for direct mounting
- High forward transfer admittance
- Excellent frequency response
- Enhancement-mode

## Outline

RENESAS Package code: PRSS0004AC-A  
(Package name: TO-220AB)



1. Gate
2. Source (Flange)
3. Drain

# Electrónica S.A. de C.V.

**2SK213, 2SK214, 2SK215, 2SK216****Absolute Maximum Ratings**

(Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK213	$V_{DSX}$	140	V
	2SK214		160	
	2SK215		180	
	2SK216		200	
Gate to source voltage		$V_{GSS}$	±15	V
Drain current		$I_D$	500	mA
Body to drain diode reverse drain current		$I_{DR}$	500	mA
Channel dissipation		Pch	1.75	W
		$Pch^{*1}$	30	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	−45 to +150	°C

Note: 1. Value at T<sub>C</sub> = 25°C**Electrical Characteristics**

(Ta = 25°C)

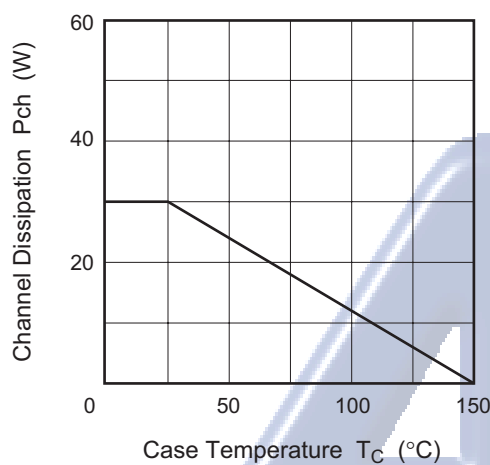
Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SK213	$V_{(BR)DSX}$	140	—	—	V	$I_D = 1 \text{ mA}, V_{GS} = -2 \text{ V}$
	2SK214		160	—	—	V	
	2SK215		180	—	—	V	
	2SK216		200	—	—	V	
Gate to source breakdown voltage		$V_{(BR)GSS}$	±15	—	—	V	$I_G = \pm 10 \text{ } \mu\text{A}, V_{DS} = 0$
Gate to source voltage		$V_{GS(on)}$	0.2	—	1.5	V	$I_D = 10 \text{ mA}, V_{DS} = 10 \text{ V}^{*2}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	2.0	V	$I_D = 10 \text{ mA}, V_{GD} = 0^{*2}$
Forward transfer admittance		$ y_{fs} $	20	40	—	mS	$I_D = 10 \text{ mA}, V_{DS} = 20 \text{ V}^{*2}$
Input capacitance		Ciss	—	90	—	pF	$I_D = 10 \text{ mA}, V_{DS} = 10 \text{ V},$ $f = 1 \text{ MHz}$
Reverse transfer capacitance		Crss	—	2.2	—	pF	

Note: 2. Pulse test

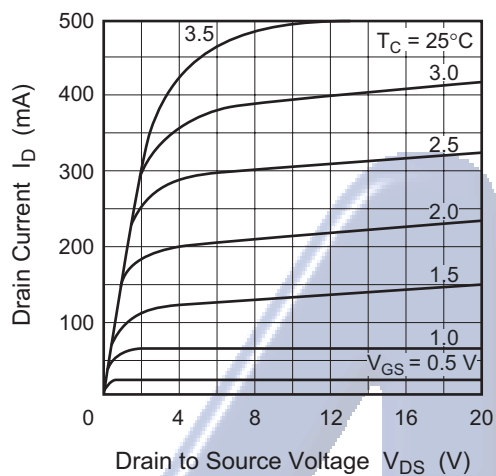
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**2SK213, 2SK214, 2SK215, 2SK216****Main Characteristics**

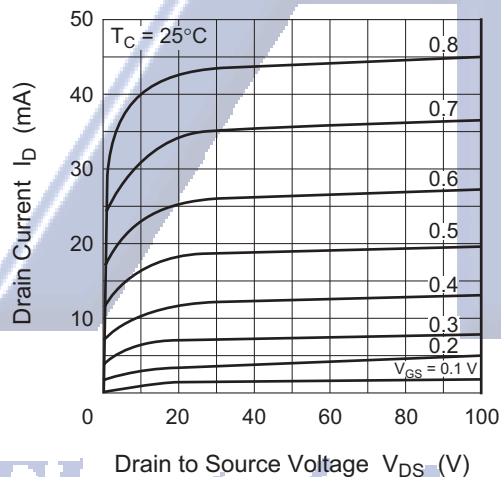
Power vs. Temperature Derating



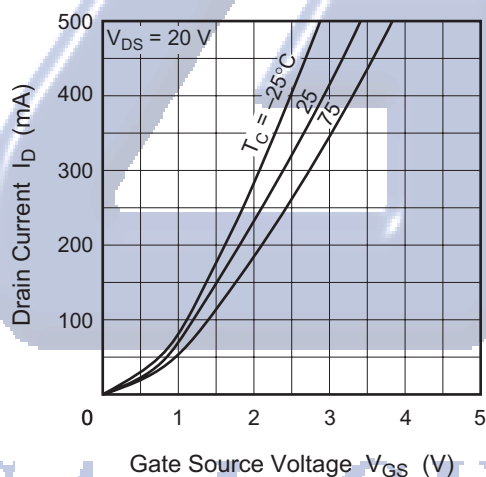
Typical Output Characteristics



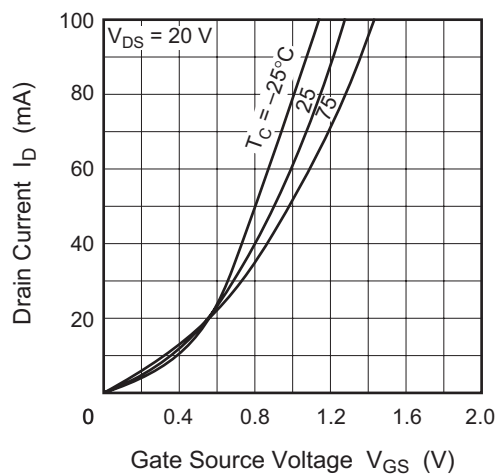
Typical Output Characteristics



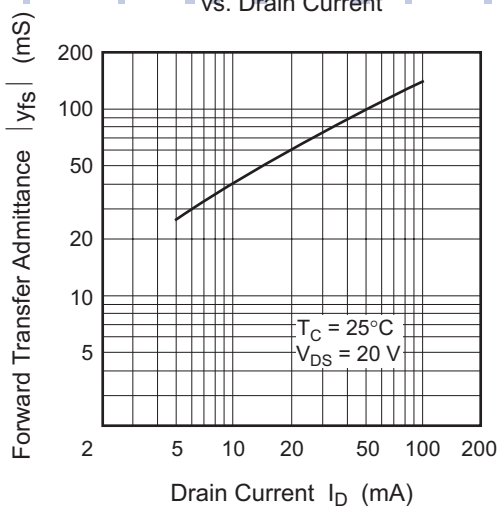
Typical Transfer Characteristics

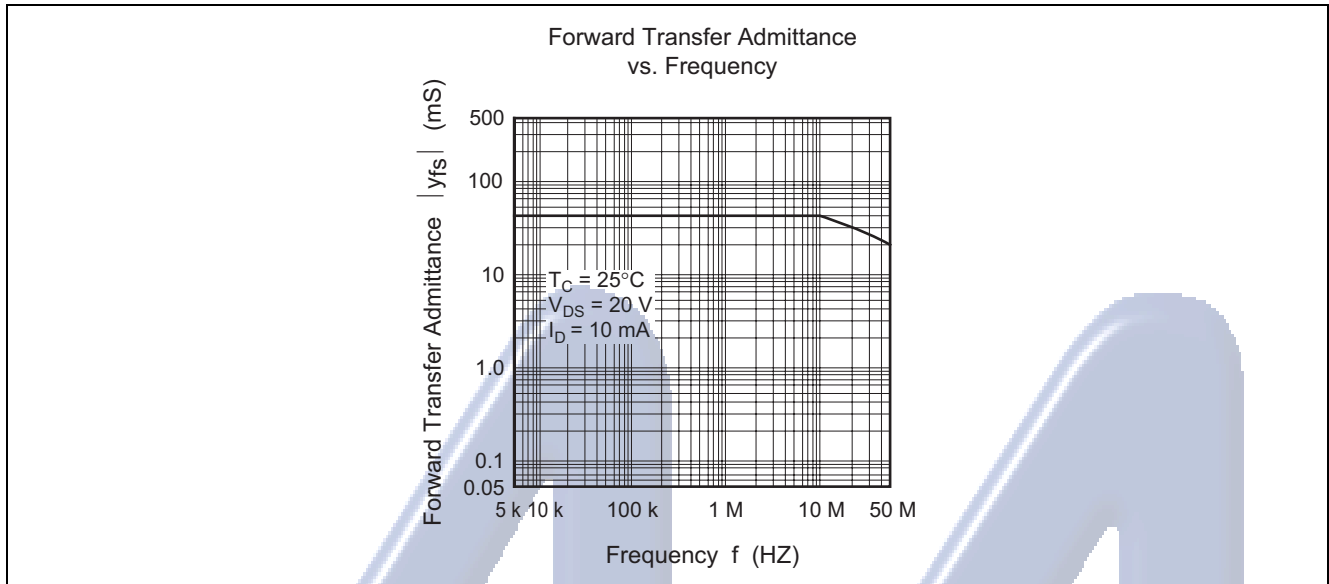


Typical Transfer Characteristics

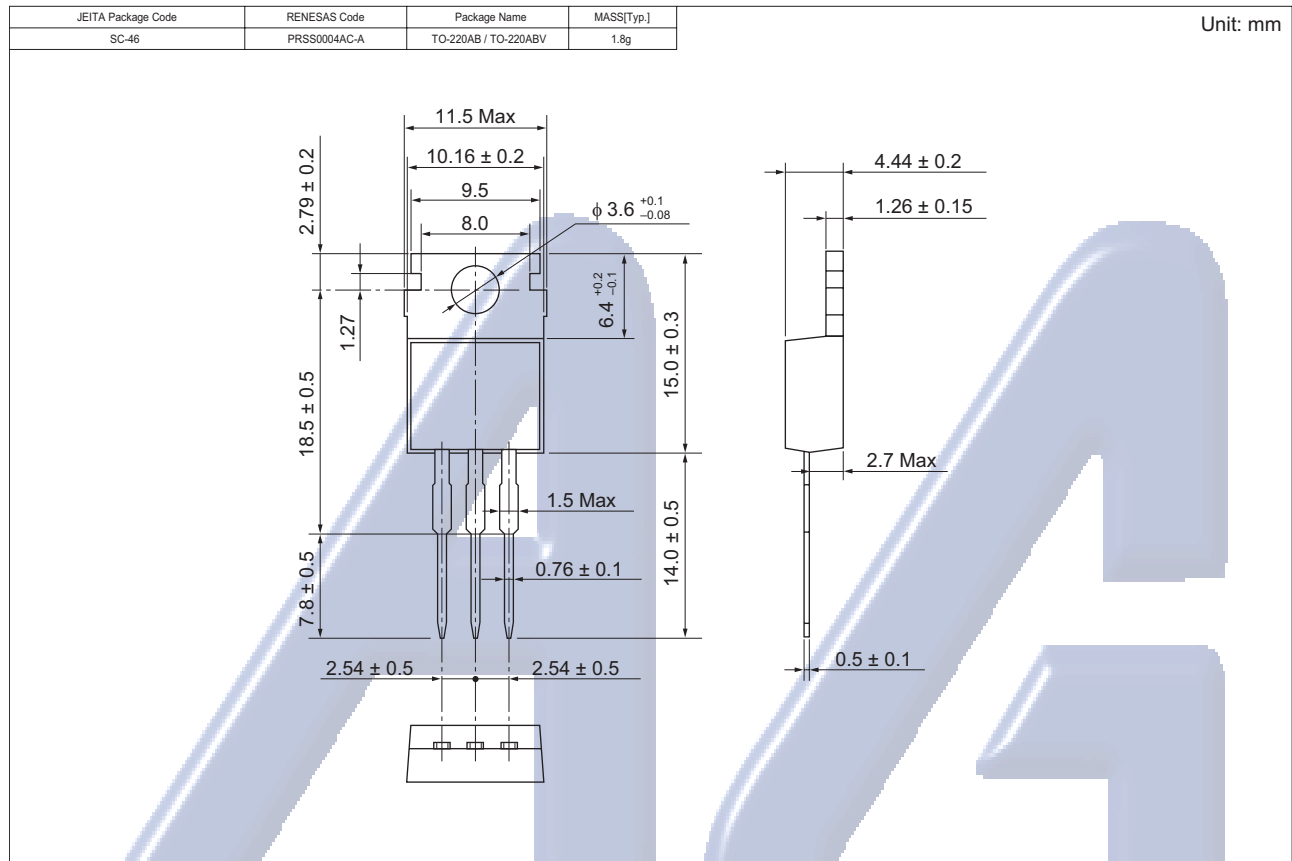


Forward Transfer Admittance vs. Drain Current



**2SK213, 2SK214, 2SK215, 2SK216**

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**2SK213, 2SK214, 2SK215, 2SK216****Package Dimensions****Ordering Information**

Part Name	Quantity	Shipping Container
2SK213-E	500 pcs	Box (Sack)
2SK214-E	500 pcs	Box (Sack)
2SK215-E	500 pcs	Box (Sack)
2SK216-E	500 pcs	Box (Sack)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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